

FAST RECOVERY RECTIFIERS

VOLTAGE RANGE: 100~600V
CURRENT: 10 A

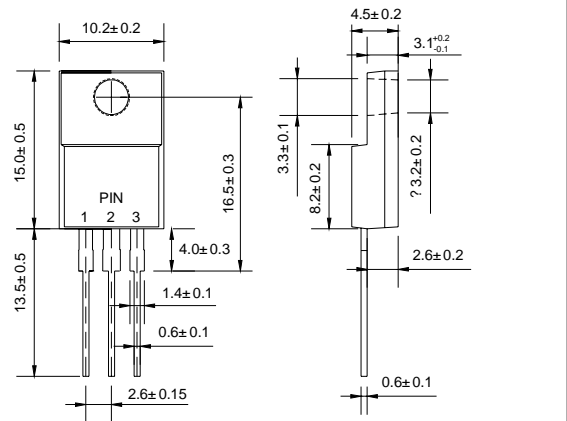
FEATURES

- ◇ Metal-Semiconductor junction with guard ring
- ◇ Epitaxial construction
- ◇ Low forward voltage drop, low switching losses
- ◇ High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case: JEDEC ITO-220AB
- ◇ Terminals: Solderable per MIL-STD-202, Method 208
- ◇ Polarity: As marked
- ◇ Weight: 0.06 ounce, 1.67 grams
- ◇ Mounting position: Any

ITO-220AB



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 50 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		FMU-21S	FMU-22S	FMU-24S	FMU-26S	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	100	200	400	600	V
Maximum RMS voltage	V_{RMS}	70	140	280	420	V
Maximum DC blocking voltage	V_{DC}	100	200	400	600	V
Maximum average forward rectified current @ $T_C=100^\circ C$	$I_{F(AV)}$	10				A
Peak forward surge current 10ms single half-sine-wave superimposed on rated load	I_{FSM}	40				A
Maximum instantaneous forward voltage ($I_F=5.0A$)	V_F	1.5				V
Maximum reverse current @ $T_J=25^\circ C$ at rated DC blocking voltage @ $T_J=100^\circ C$	I_R	50 500				μA
Maximum reverse recovery time (Note1)	t_{rr}	180				ns
Typical thermal resistance (Note2)	$R_{\theta JC}$	4.0				$^\circ C/W$
Operating junction temperature range	T_J	- 55 ---- + 150				$^\circ C$
Storage temperature range	T_{STG}	- 55 ---- + 150				$^\circ C$

NOTE: 1. Measured with $I_F=0.5A$, $I_R=1A$, $I_{rr}=0.25A$.
2. Thermal resistance junction to case.

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FIG.1 – TYPICAL FORWARD CHARACTERISTIC

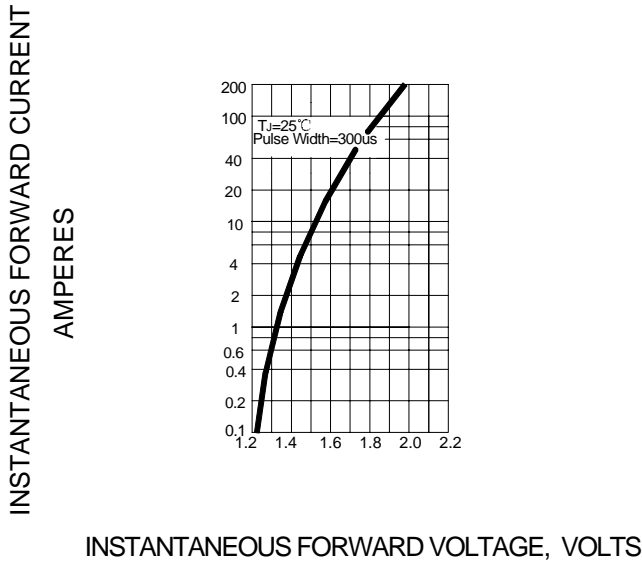


FIG.2- FORWARD DERATING CURVE

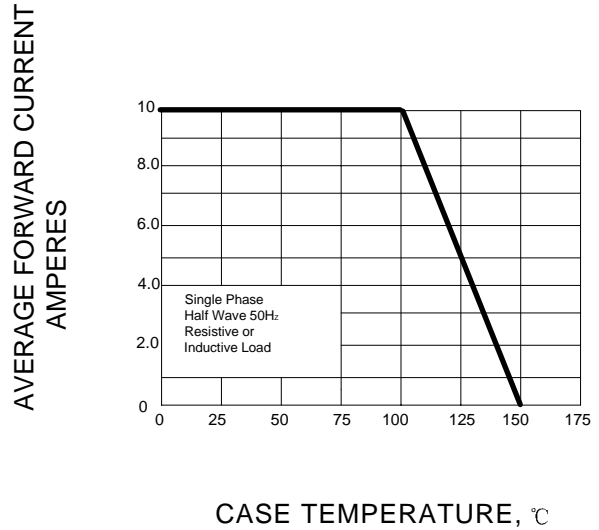


FIG.3- PEAK FORWARD SURGE CURRENT

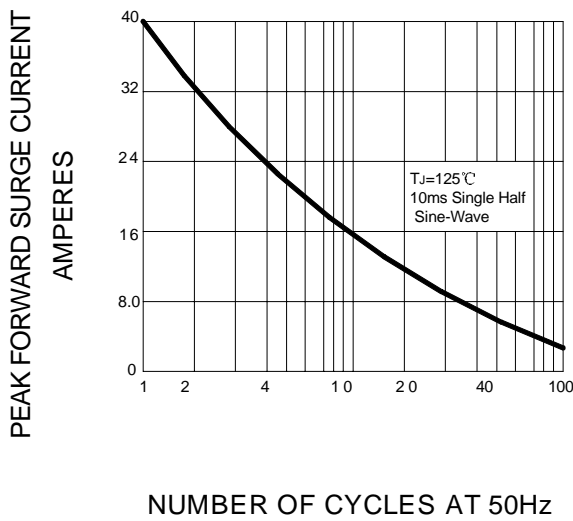


FIG.4 – TYPICAL REVERSE CHARACTERISTICS

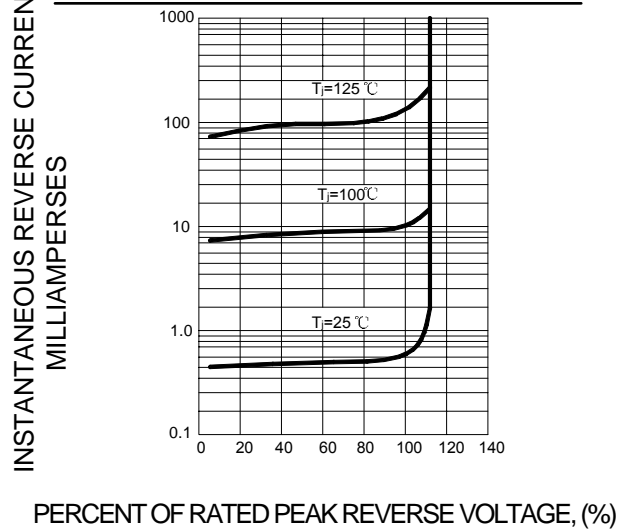
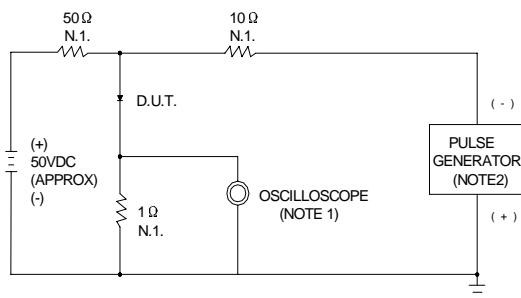


FIG.5 – REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



NOTES: 1. RISE TIME=7ns MAX. INPUT IMPEDANCE=1MΩ, 22pF
2. RISE TIME=10ns MAX. SOURCE IMPEDANCE=50Ω

